

TO-92 Plastic-Encapsulate Transistors

2N4401052

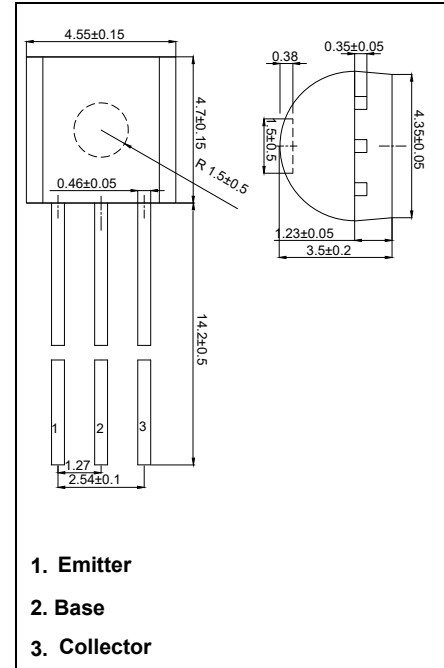
NPN Silicon

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V _{CEO}	Collector – Emitter Voltage	40	Vdc
V _{CBO}	Collector – Base Voltage	60	Vdc
V _{EBO}	Emitter – Base Voltage	6.0	Vdc
I _C	Collector Current – Continuous	600	mAdc
P _D	Total Device Dissipation @ T _A = 25°C Derate above 25°C	625 5.0	mW mW/°C
P _D	Total Device Dissipation @ T _C = 25°C Derate above 25°C	1.5 12	W mW/°C
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C



THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
R _{θJA}	Thermal Resistance, Junction-to-Ambient	200	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
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OFF CHARACTERISTICS

V _{(BR)CEO}	Collector–Emitter Breakdown Voltage (Note 1)	(I _C = 1.0 mAdc, I _B = 0)	40	-	Vdc
V _{(BR)CBO}	Collector–Base Breakdown Voltage	(I _C = 0.1 mAdc, I _E = 0)	60	-	Vdc
V _{(BR)EBO}	Emitter–Base Breakdown Voltage	(I _E = 0.1 mAdc, I _C = 0)	6.0	-	Vdc
I _{BEV}	Base Cutoff Current	(V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	-	0.1	μAdc
I _{CEX}	Collector Cutoff Current	(V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	-	0.1	μAdc

ON CHARACTERISTICS (Note 1)

h _{FE}	DC Current Gain	(I _C = 0.1 mAdc, V _{CE} = 1.0 Vdc) (I _C = 1.0 mAdc, V _{CE} = 1.0 Vdc) (I _C = 10 mAdc, V _{CE} = 1.0 Vdc) (I _C = 150 mAdc, V _{CE} = 1.0 Vdc) (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)	20 40 80 100 40	- - - 300 -	-
V _{CE(sat)}	Collector–Emitter Saturation Voltage	(I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	- -	0.4 0.75	Vdc
V _{BE(sat)}	Base–Emitter Saturation Voltage	(I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	0.75 -	0.95 1.2	Vdc

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
f_T	Current-Gain – Bandwidth Product ($I_C = 20\text{ mA dc}$, $V_{CE} = 10\text{ V dc}$, $f = 100\text{ MHz}$)	250	–	MHz
C_{cb}	Collector-Base Capacitance ($V_{CB} = 5.0\text{ V dc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	–	6.5	pF
C_{eb}	Emitter-Base Capacitance ($V_{EB} = 0.5\text{ V dc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	–	30	pF
h_{ie}	Input Impedance ($I_C = 1.0\text{ mA dc}$, $V_{CE} = 10\text{ V dc}$, $f = 1.0\text{ kHz}$)	1.0	15	k Ω
h_{re}	Voltage Feedback Ratio ($I_C = 1.0\text{ mA dc}$, $V_{CE} = 10\text{ V dc}$, $f = 1.0\text{ kHz}$)	0.1	8.0	$\times 10^{-4}$
h_{fe}	Small-Signal Current Gain ($I_C = 1.0\text{ mA dc}$, $V_{CE} = 10\text{ V dc}$, $f = 1.0\text{ kHz}$)	40	500	–
h_{oe}	Output Admittance ($I_C = 1.0\text{ mA dc}$, $V_{CE} = 10\text{ V dc}$, $f = 1.0\text{ kHz}$)	1.0	30	μmhos

SWITCHING CHARACTERISTICS

t_d	Delay Time	($V_{CC} = 30\text{ V dc}$, $V_{BE} = 2.0\text{ V dc}$, $I_C = 150\text{ mA dc}$, $I_{B1} = 15\text{ mA dc}$)	–	15	ns
t_r	Rise Time		–	20	ns
t_s	Storage Time	($V_{CC} = 30\text{ V dc}$, $I_C = 150\text{ mA dc}$, $I_{B1} = I_{B2} = 15\text{ mA dc}$)	–	225	ns
t_f	Fall Time		–	30	ns

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

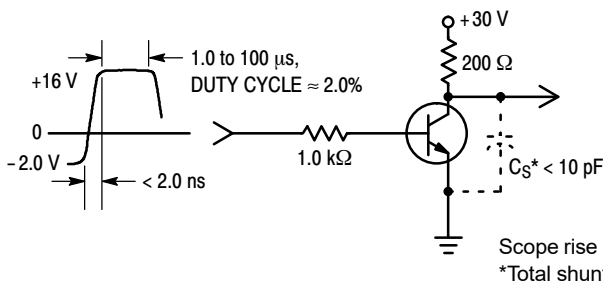


Figure 1. Turn-On Time

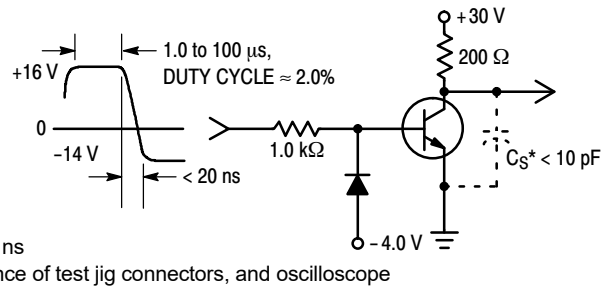


Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

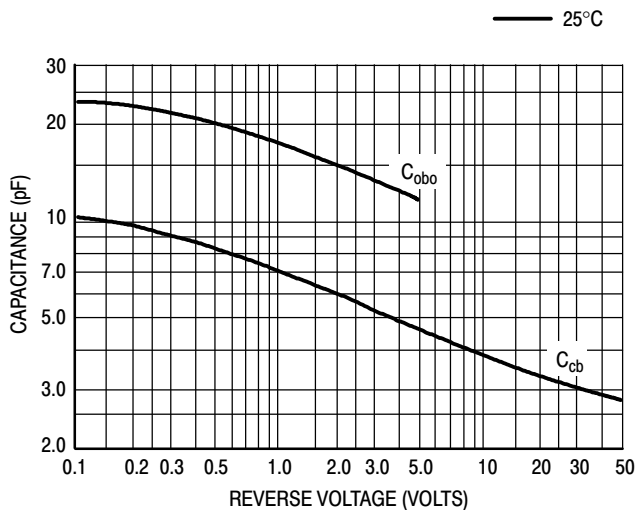


Figure 3. Capacitances

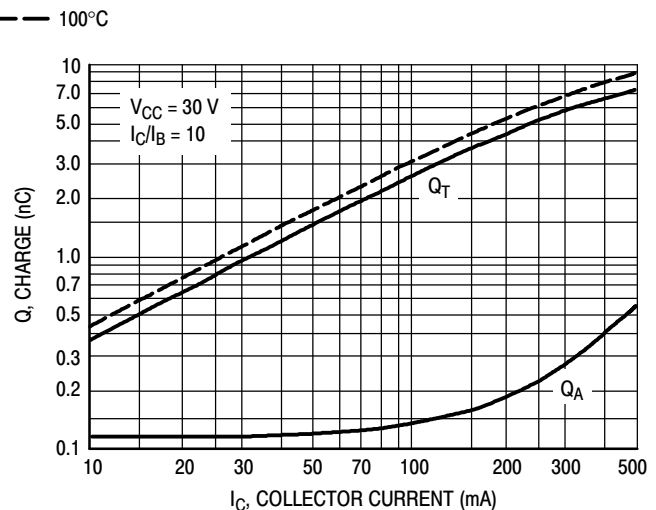


Figure 4. Charge Data

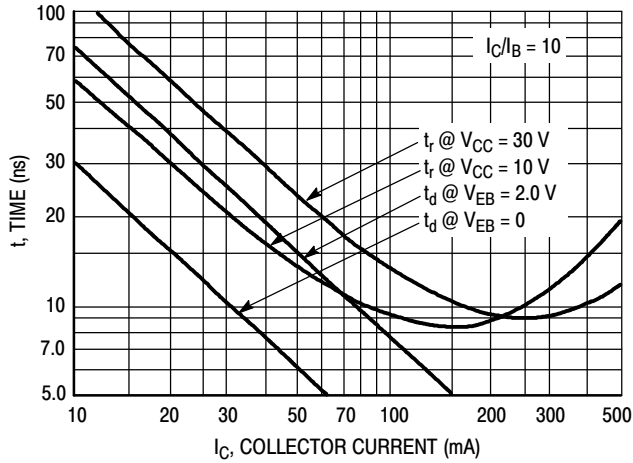


Figure 5. Turn-On Time

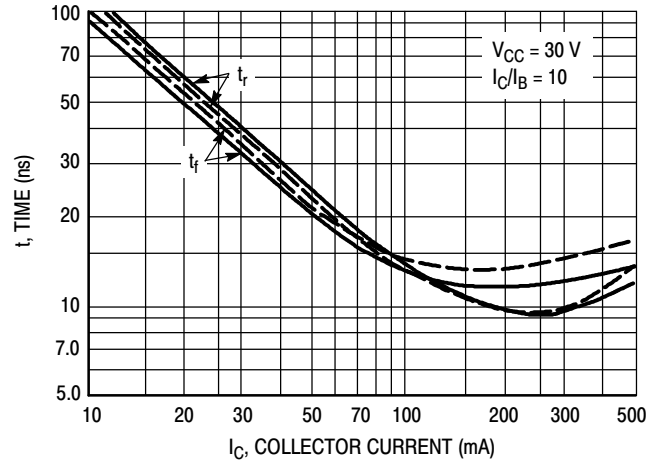


Figure 6. Rise and Fall Times

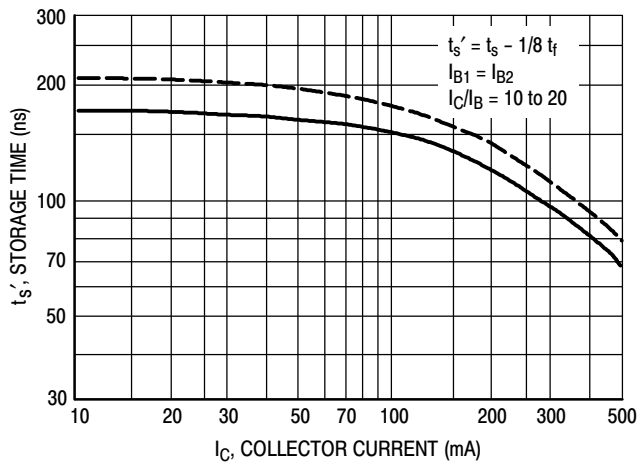


Figure 7. Storage Time

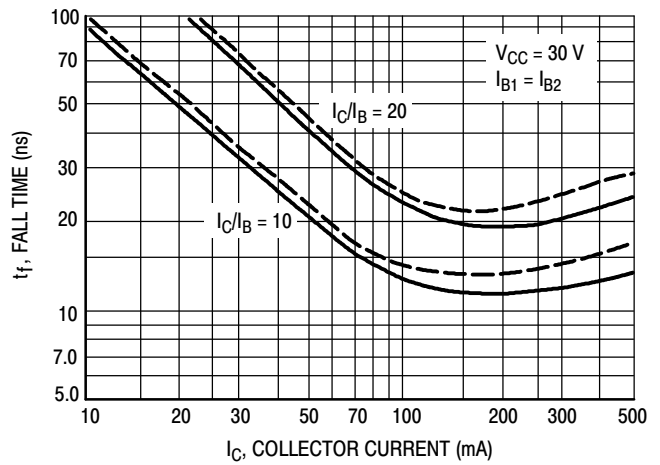


Figure 8. Fall Time

**SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE**

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$; Bandwidth = 1.0 Hz

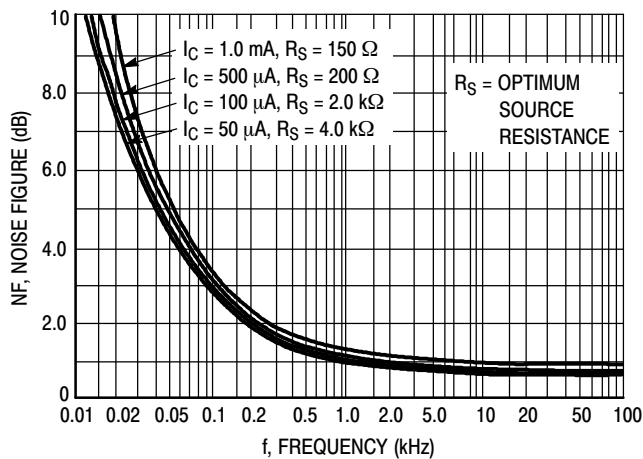


Figure 9. Frequency Effects

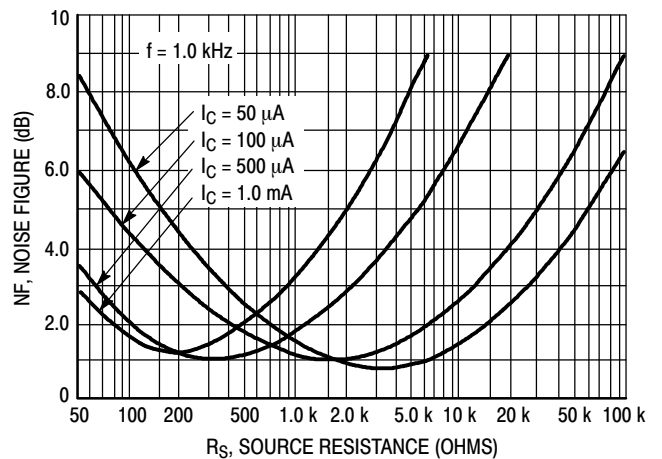


Figure 10. Source Resistance Effects

h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between h_{fe} and other “h” parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were

selected from the 2N4401 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

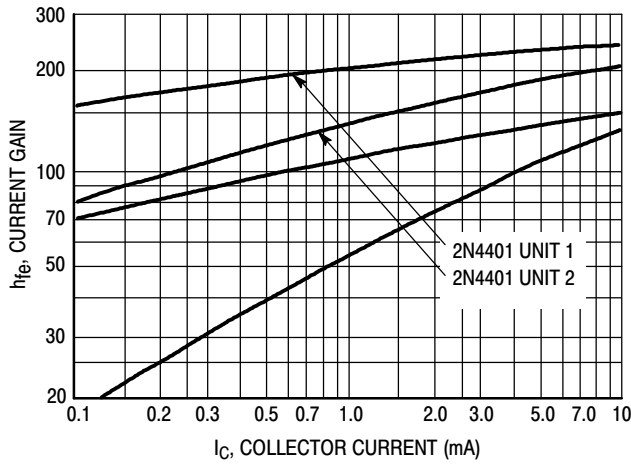


Figure 11. Current Gain

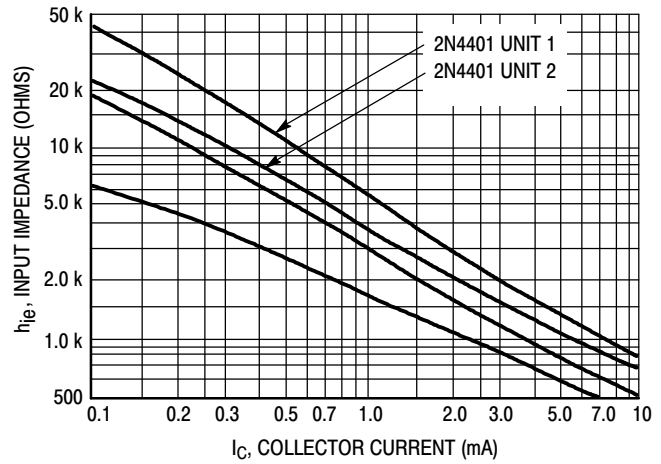


Figure 12. Input Impedance

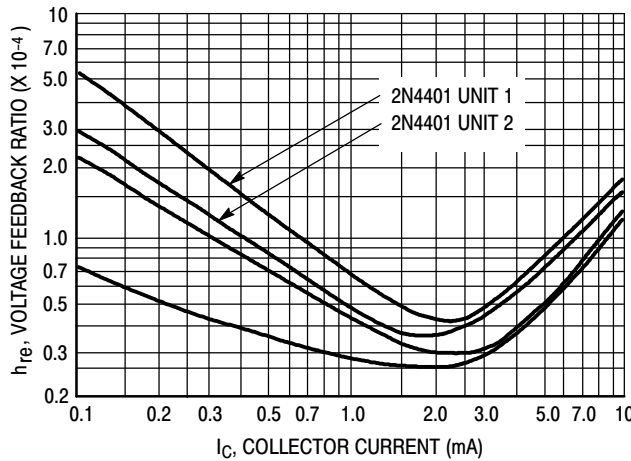


Figure 13. Voltage Feedback Ratio

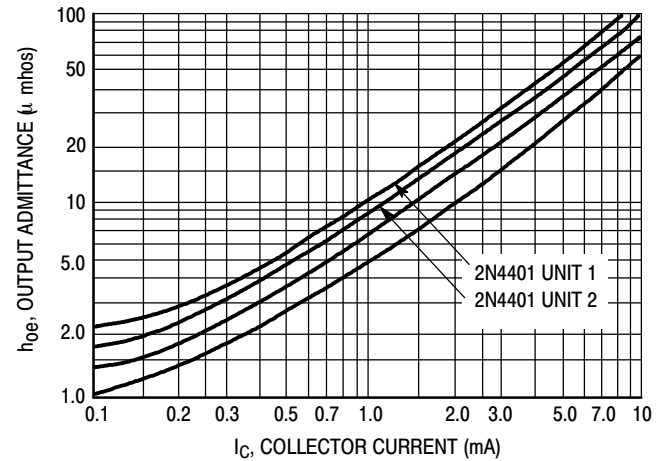


Figure 14. Output Admittance

STATIC CHARACTERISTICS

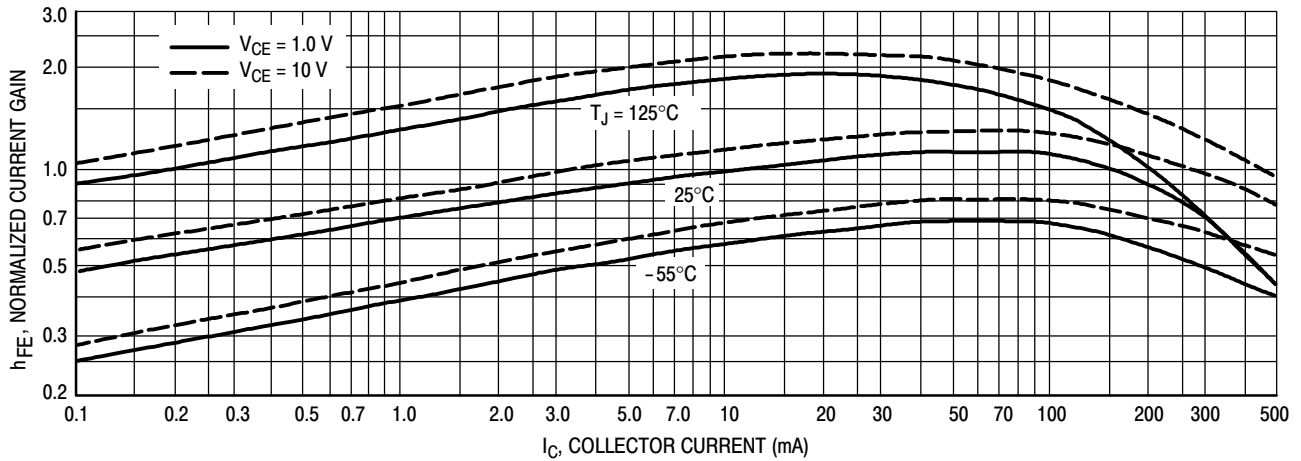


Figure 15. DC Current Gain

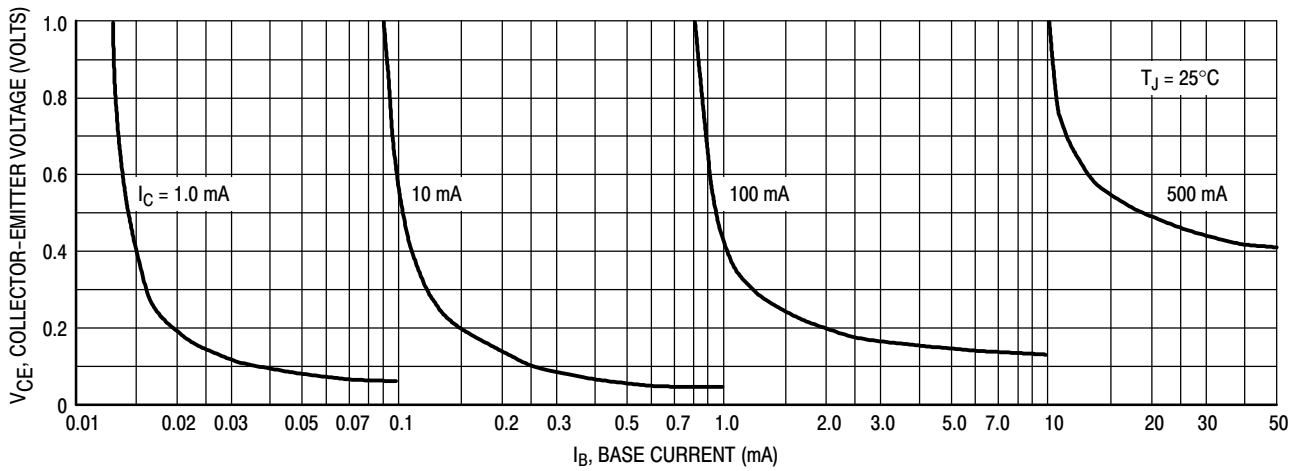


Figure 16. Collector Saturation Region

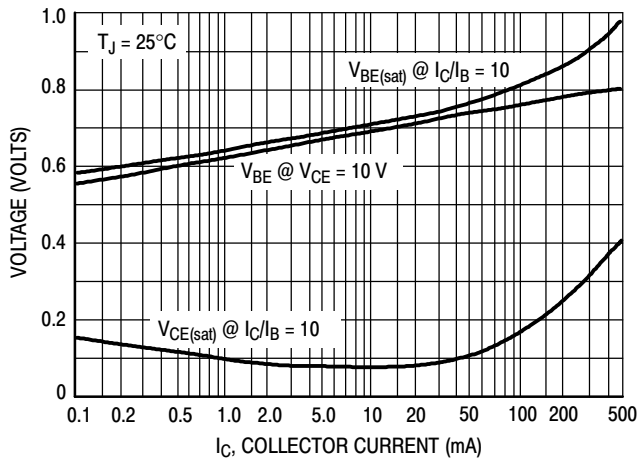


Figure 17. "On" Voltages

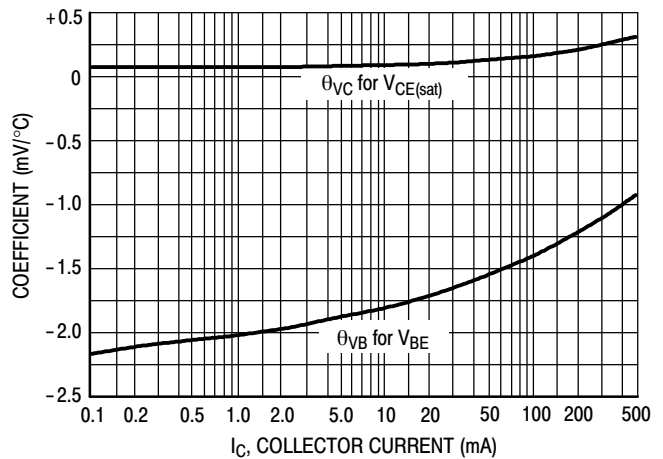


Figure 18. Temperature Coefficients

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